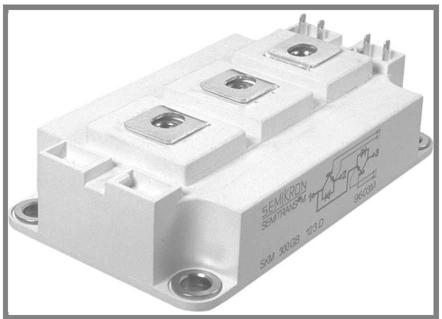
SKM 300GB123D



SEMITRANS™ 3

IGBT Modules

SKM 300GB123D

SKM 300GAL123D

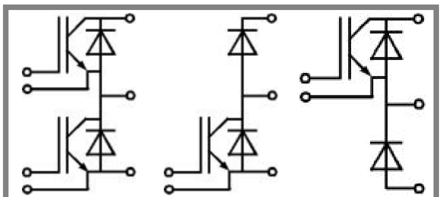
SKM 300GAR123D

Features

- MOS input (voltage controlled)
- N channel , Homogeneous Si
- Low inductance case
- Very low tail current with low temperature dependence
- High short circuit capability, self limiting to 6 x I_{cnom}
- Latch-up free
- Fast & soft inverse CAL diodes
- Isolated copper baseplate using DCB Direct Copper Bonding Technology
- Large clearance (12 mm) and creepage distance (20 mm)

Typical Applications

- Switching (not for linear use)
- AC inverter drives
- UPS



GB GAL GAR

Absolute Maximum Ratings	T_c = 25 °C, unless otherwise specified		
Symbol	**Conditions**	**Values**	**Units**
IGBT			
V_{CES}		1200	V
I_C	T_c = 25 (80) °C	300 (220)	A
I_{CRM}	T_c = 25 (80) °C, t_p = 1 ms	600 (440)	A
V_{GES}		± 20	V
T_{vj}, (T_{stg})	$T_{OPERATION} \leq T_{stg}$	- 40 ... + 150 (125)	°C
V_{isol}	AC, 1 min.	2500	V
Inverse diode			
I_F	T_c = 25 (80) °C	260 (180)	A
I_{FRM}	T_c = 25 (80) °C, t_p = 1 ms	600 (440)	A
I_{FSM}	t_p = 10 ms; sin.; T_j = 150 °C	2200	A
Freewheeling diode			
I_F	T_c = 25 (80) °C	350 (230)	A
I_{FRM}	T_c = 25 (80) °C, t_p = 1 ms	600 (440)	A
I_{FSM}	t_p = 10 ms; sin; T_j = 150 °C	2900	A

Characteristics	T_c = 25 °C, unless otherwise specified				
Symbol	**Conditions**	**min.**	**typ.**	**max.**	**Units**
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}$, I_C = 8 mA	4,5	5,5	6,5	V
I_{CES}	V_{GE} = 0, $V_{CE} = V_{CES}$, T_j = 25 (125) °C		0,1	0,3	mA
$V_{CE(TO)}$	T_j = 25 (125) °C		1,4 (1,6)	1,6 (1,8)	V
r_{CE}	V_{GE} = 15 V, T_j = 25 (125) °C		5,5 (7,5)	7 (9,5)	mΩ
$V_{CE(sat)}$	I_C = 200 A, V_{GE} = 15 V, chip level		2,5 (3,1)	3 (3,7)	V
C_{ies}	under following conditions		18	24	nF
C_{oes}	V_{GE} = 0, V_{CE} = 25 V, f = 1 MHz		2,5	3,2	nF
C_{res}			1	1,3	nF
L_{CE}				20	nH
$R_{CC'+EE'}$	res., terminal-chip T_c= 25 (125) °C		0,35 (0,5)		mΩ
$t_{d(on)}$	V_{CC} = 600 V, I_C = 200 A		250	400	ns
t_r	$R_{Gon} = R_{Goff}$ = 4,7 Ω, T_j = 125 °C		90	160	ns
$t_{d(off)}$	V_{GE} = ± 15 V		550	700	ns
t_f			70	100	ns
E_{on} (E_{off})			28 (26)		mJ
Inverse diode					
$V_F = V_{EC}$	I_F = 200 A; V_{GE} = 0 V; T_j = 25 (125) °C		2 (1,8)	2,5	V
$V_{(TO)}$	T_j = 125 () °C		1,1	1,2	V
r_T	T_j = 125 () °C		3	5,5	mΩ
I_{RRM}	I_F = 200 A; T_j = 25 (125) °C		70 (105)		A
Q_{rr}	di/dt = A/µs		10 (26)		µC
E_{rr}	V_{GE} = V				mJ
FWD					
$V_F = V_{EC}$	I_F = 200 A; V_{GE} = 0 V, T_j = 25 (125) °C		1,9 (1,7)	2,4	V
$V_{(TO)}$	T_j = 125 () °C			1,2	V
r_T	T_j = 125 () °C		3	3,5	mΩ
I_{RRM}	I_F = 200 A; T_j = 25 (125) °C		80 (140)		A
Q_{rr}	di/dt = A/µs		10 (34)		µC
E_{rr}	V_{GE} = V				mJ
Thermal characteristics					
$R_{th(j-c)}$	per IGBT			0,075	K/W
$R_{th(j-c)D}$	per Inverse Diode			0,18	K/W
$R_{th(j-c)FD}$	per FWD			0,15	K/W
$R_{th(c-s)}$	per module			0,038	K/W
Mechanical data					
M_s	to heatsink M6	3		5	Nm
M_t	to terminals M6				Nm
w				325	g

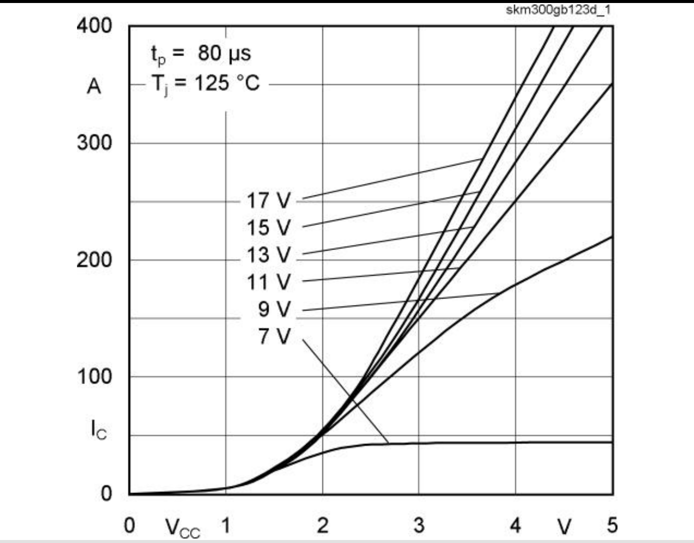


Fig. 1 Typ. output characteristic, inclusive $R_{CC'+EE'}$

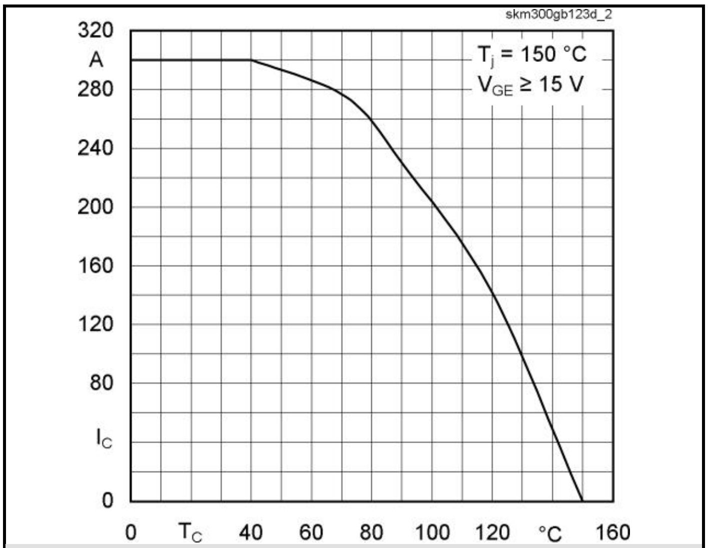


Fig. 2 Rated current vs. temperature $I_C = f(T_C)$

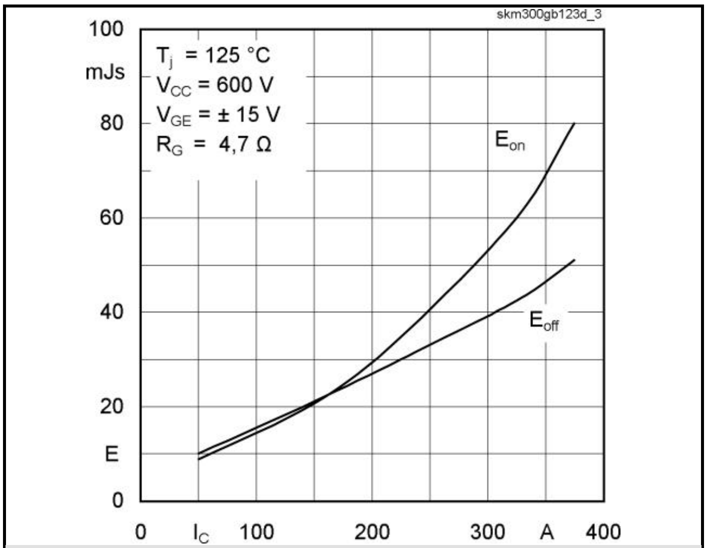


Fig. 3 Typ. turn-on /-off energy = f (I_C)

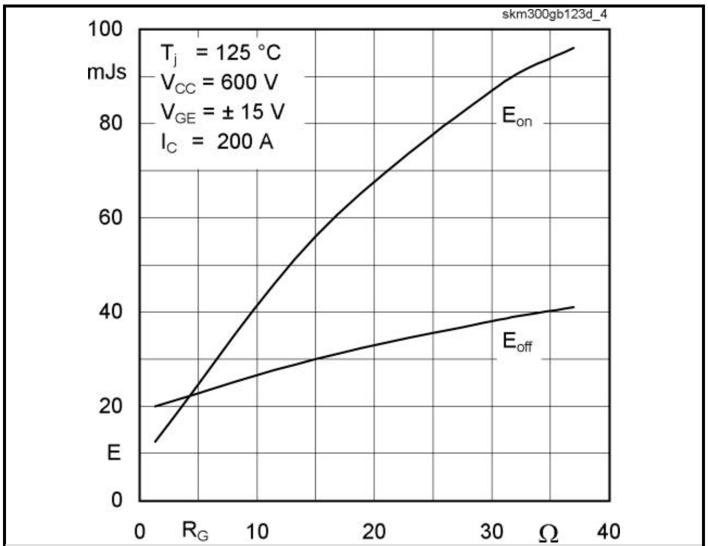


Fig. 4 Typ. turn-on /-off energy = f (R_G)

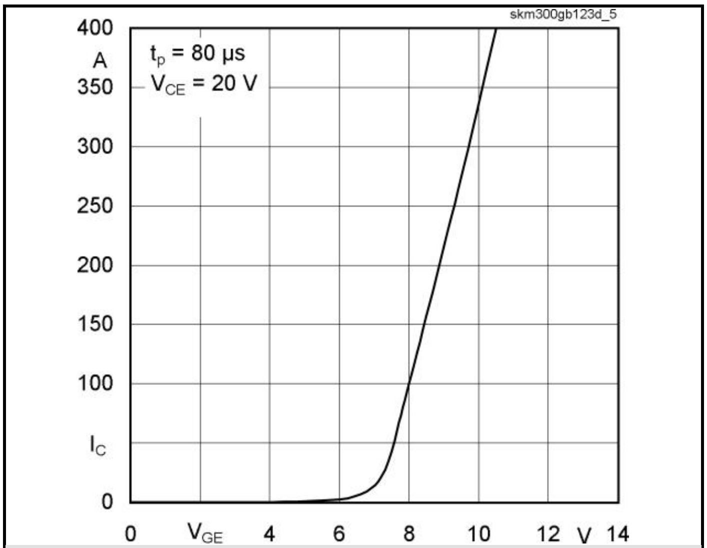


Fig. 5 Typ. transfer characteristic

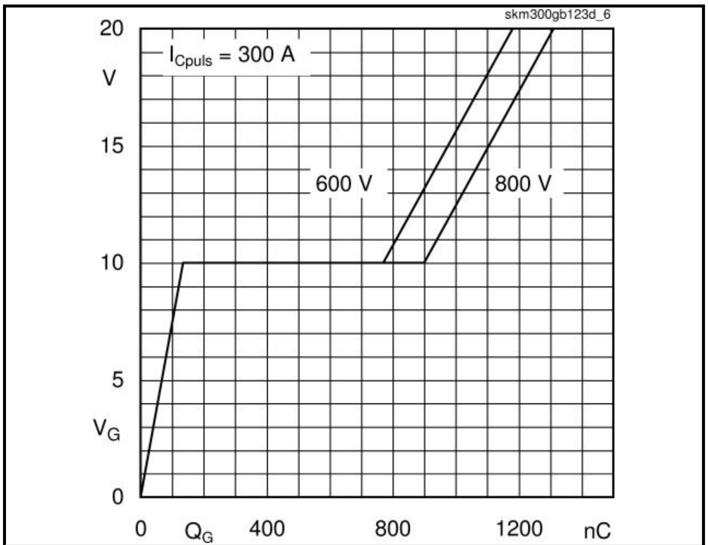


Fig. 6 Typ. gate charge characteristic

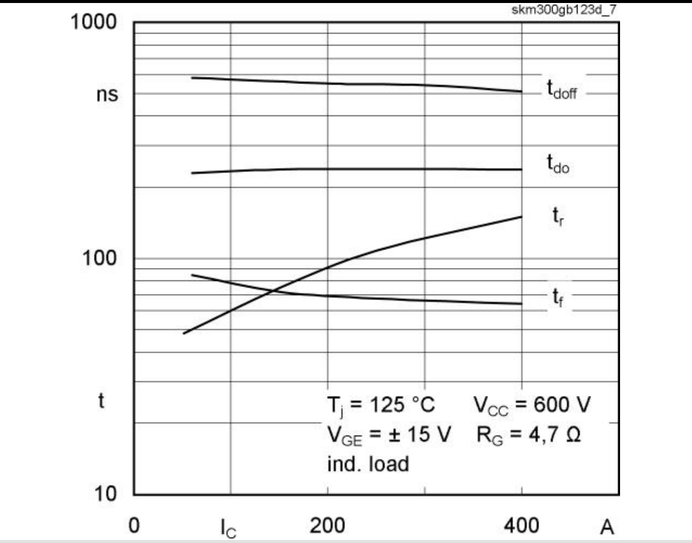


Fig. 7 Typ. switching times vs. I_C

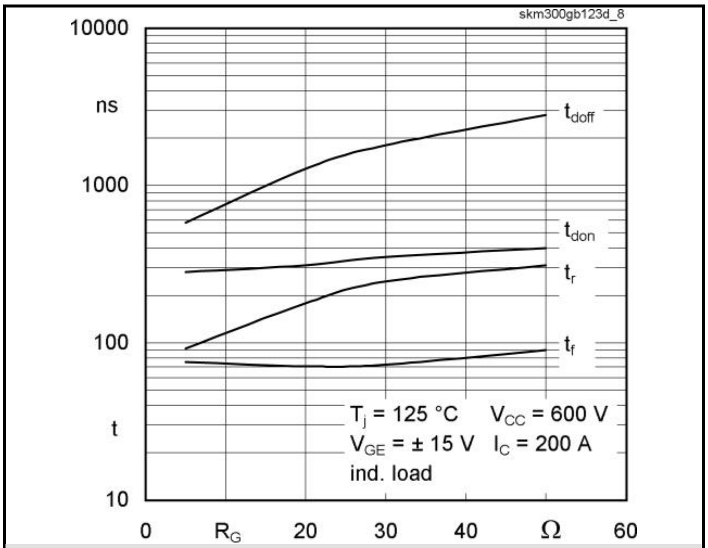


Fig. 8 Typ. switching times vs. gate resistor R_G

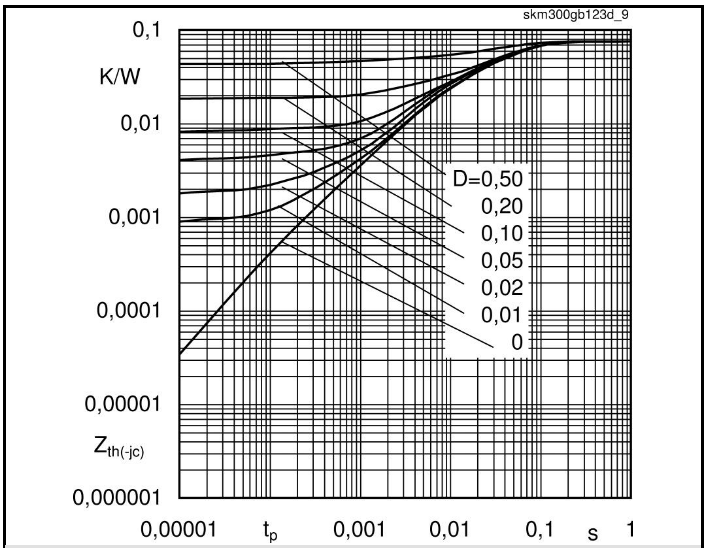


Fig. 9 Transient thermal impedance of IGBT

$Z_{thp(j-c)} = f(t_p)$; $D = t_p/t_c = t_p*f$

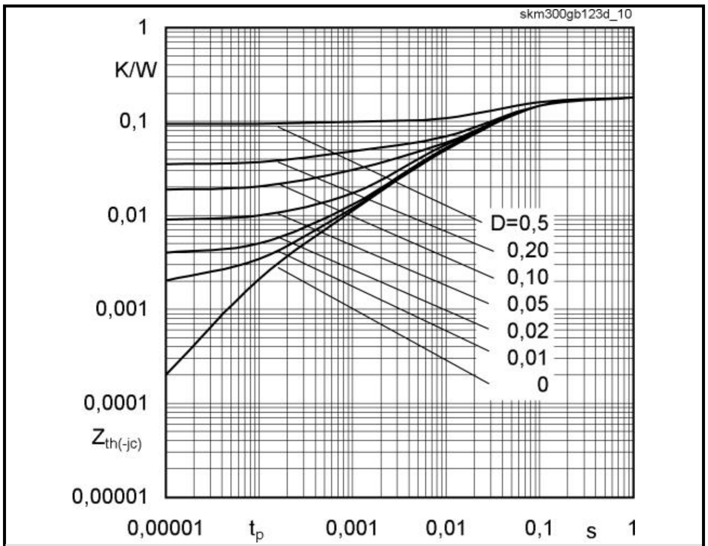


Fig. 10 Transient thermal impedance of FWD

$Z_{thp(j-c)} = f(t_p)$; $D = t_p/t_c = t_p*f$

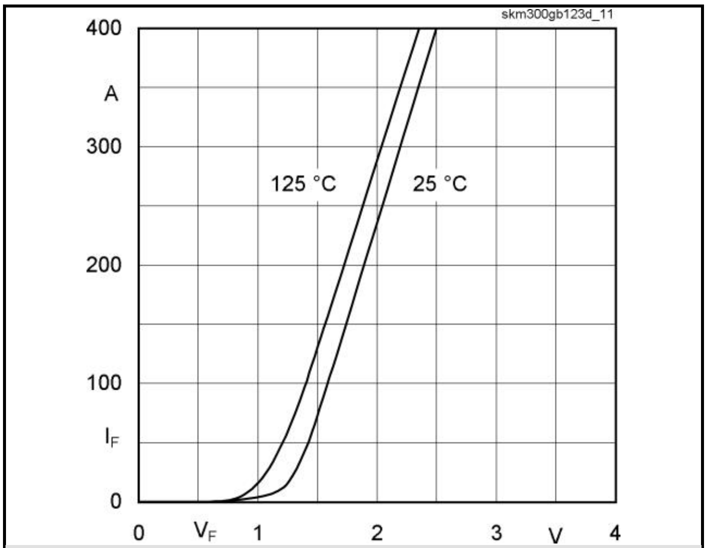


Fig. 11 CAL diode forward characteristic

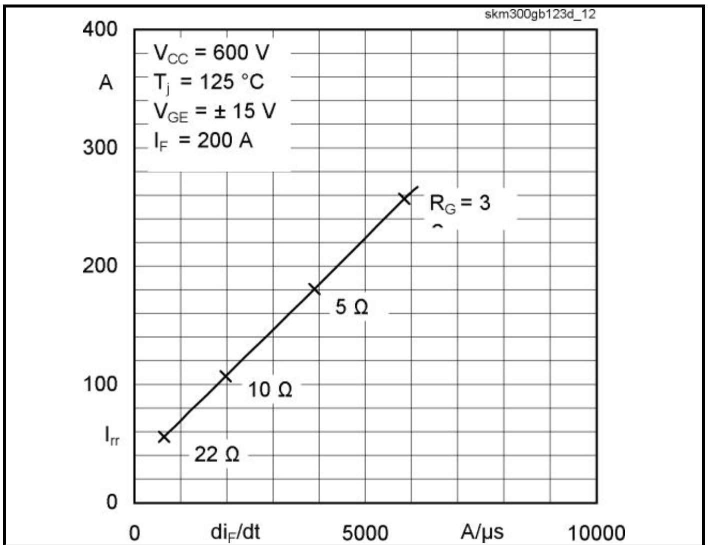


Fig. 12 Typ. CAL diode peak reverse recovery current

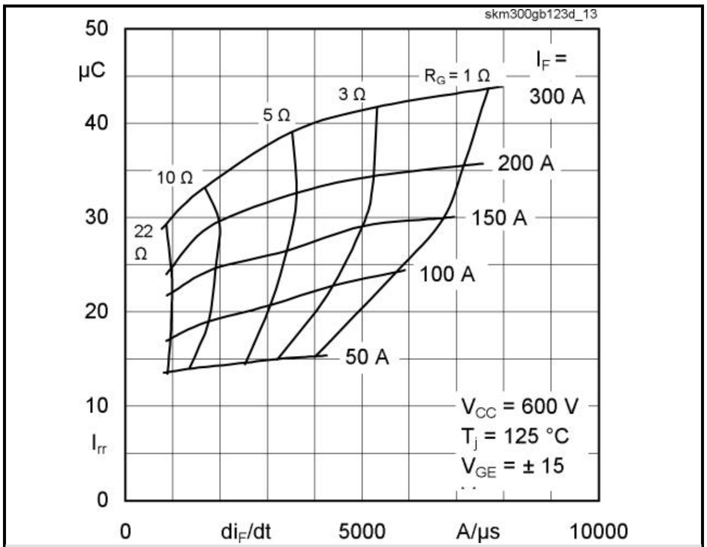
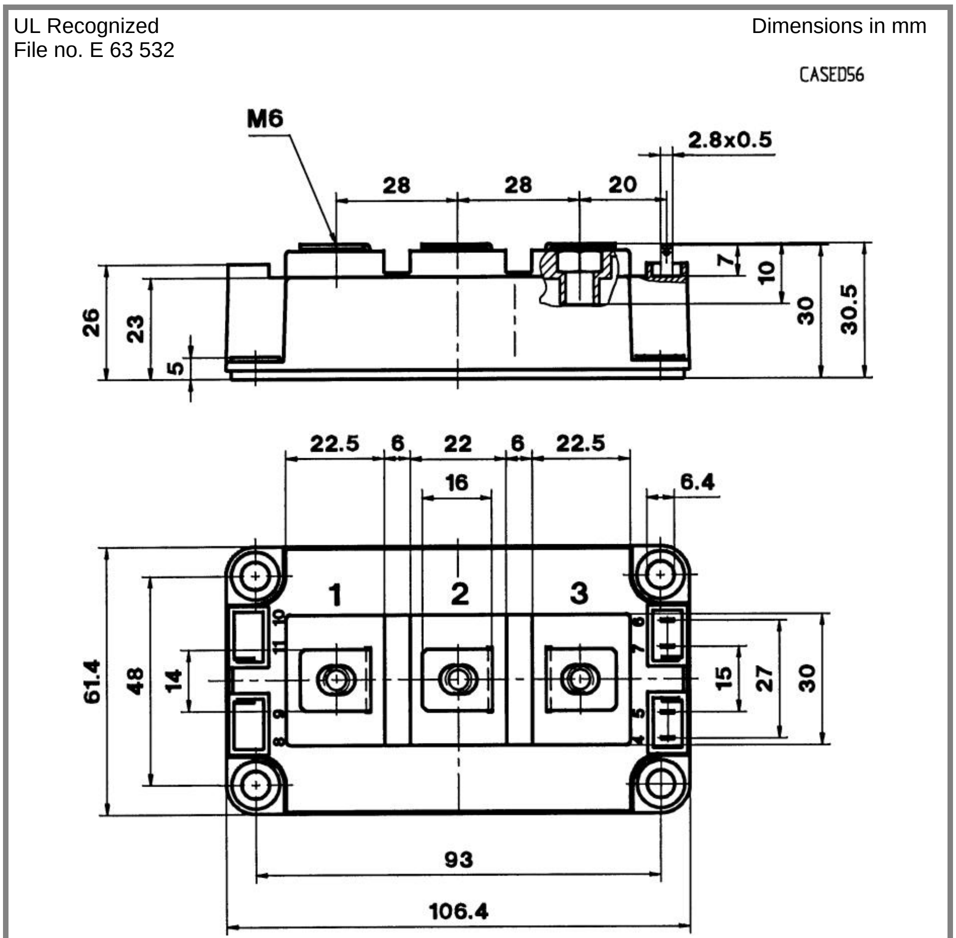
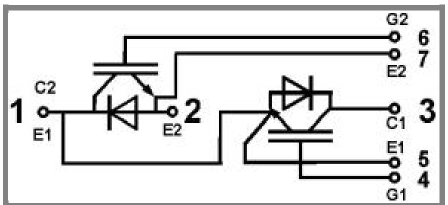


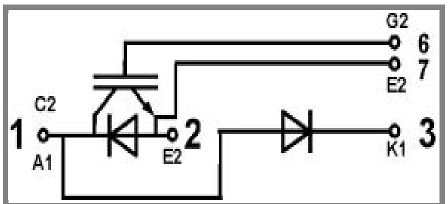
Fig. 13 Typ. CAL diode recovered charge



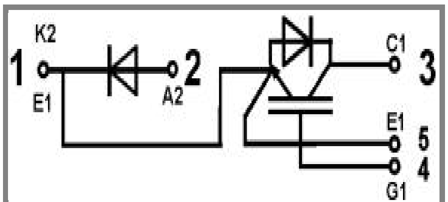
Case D 56



GB Case D 56



GAL Case D 57 (➞ D 56)



GAR Case D 58 (➞ D 56)

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.